

EMT2 / EMT3 / UMT2N / IMT2A / IMT3A

Transistors

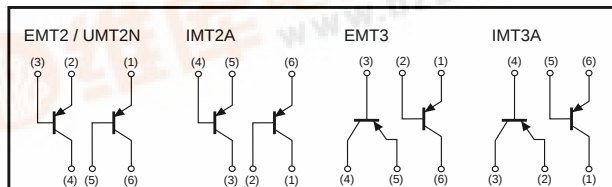
General purpose (dual transistors)

EMT2 / EMT3 / UMT2N / IMT2A / IMT3A

●Features

1) Two 2SA1037AK chips in a EMT or UMT or SMT package.

●Equivalent circuits



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CB0}	-60	V
Collector-emitter voltage	V_{CE0}	-50	V
Emitter-base voltage	V_{EB0}	-6	V
Collector current	I_C	150	mA
Collector power dissipation	EMT2 / EMT3 / UMT2N	150(TOTAL)	mW *1
	IMT2A / IMT3A	300(TOTAL)	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~+150	°C

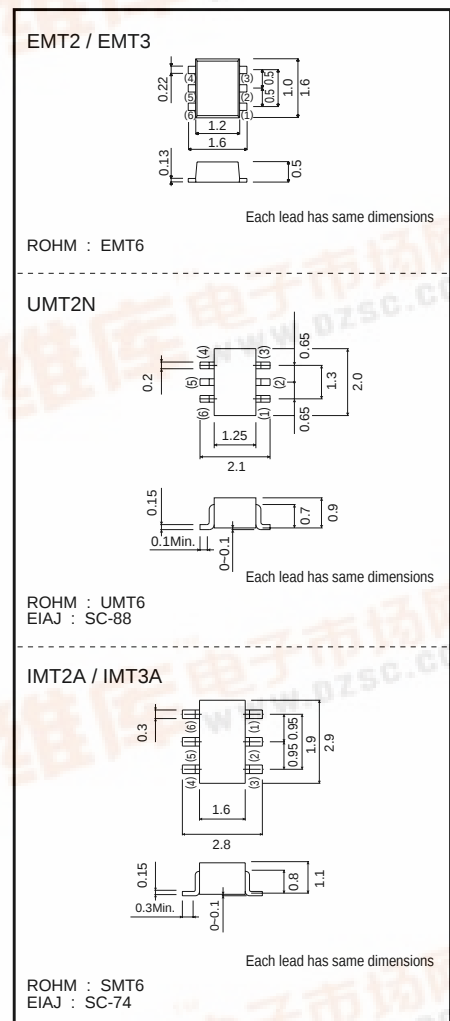
*1 120mW per element must not be exceeded.

*2 200mW per element must not be exceeded.

●Package, marking, and packaging specifications

Type	EMT2	EMT3	UMT2N	IMT2A	IMT3A
Package	EMT6	EMT6	UMT6	SMT6	SMT6
Marking	T2	T3	T2	T2	T3
Code	T2R	T2R	TR	T108	T108
Basic ordering unit (pieces)	8000	8000	3000	3000	3000

●External dimensions (Units : mm)



●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CB0}	-60	-	-	V	$I_C = -50\mu A$
Collector-emitter breakdown voltage	BV_{CE0}	-50	-	-	V	$I_C = -1mA$
Emitter-base breakdown voltage	BV_{EB0}	-6	-	-	V	$I_E = -50\mu A$
Collector cutoff current	I_{CBO}	-	-	-0.1	μA	$V_{CB} = -60V$
Emitter cutoff current	I_{EBO}	-	-	-0.1	μA	$V_{EB} = -6V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	-0.5	V	$I_C/I_E = -50mA/-5mA$
DC current transfer ratio	h_{FE}	120	-	560	-	$V_{CE} = -6V, I_C = -1mA$
Transition frequency	f_T	-	140	-	MHz	$V_{CE} = -12V, I_E = 2mA, f = 100MHz$ *
Output capacitance	C_{ob}	-	4	5	pF	$V_{CE} = -12V, I_E = 0A, f = 1MHz$

*Transition frequency of the device.